

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











NPN LOW POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/368

Qualified Levels: JAN, JANTX, JANTXV and JANS

DESCRIPTION

This family of high-frequency, epitaxial planar transistors feature low saturation voltage. These devices are also available in TO-39 and low profile U4 and UA packaging. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- JEDEC registered 2N3439L through 2N3440L series.
- JAN, JANTX, JANTXV, and JANS qualifications are available per MIL-PRF-19500/368.
- RoHS compliant versions available (commercial grade only).
- $V_{CE(sat)} = 0.5 \text{ V} @ I_C = 50 \text{ mA}.$
- Turn-On time $t_{on} = 1.0 \mu s max @ I_C = 20 mA$, $I_{B1} = 2.0 mA$.
- Turn-Off time $t_{off} = 10 \mu s max @ I_C = 20 mA, I_{B1} = -I_{B2} = 2.0 mA.$

APPLICATIONS / BENEFITS

- General purpose transistors for medium power applications requiring high frequency switching and low package profile.
- Military and other high-reliability applications.



TO-5 Package

Also available in:

TO-39 (TO-205AD) package (leaded)

(leaded) 2N3439 – 2N3440

U4 package (surface mount) 2N3439U4 – 2N3440U4

MAXIMUM RATINGS ($T_C = +25^{\circ}C$ unless otherwise noted)

Parameters / Test Conditions	Symbol	2N3439L	2N3440L	Unit
Collector-Emitter Voltage	V _{CEO}	350	250	٧
Collector-Base Voltage	V _{CBO}	450	300	٧
Emitter-Base Voltage	V _{EBO}	7.0		٧
Collector Current	Ic	1.0		Α
Total Power Dissipation @ $T_A = +25 ^{\circ}C^{(1)}$ @ $T_C = +25 ^{\circ}C^{(2)}$	P _D	0.8 5.0		W
Operating & Storage Junction Temperature Rar	nge T _J , T _{stg}	-65 to	+200	°C

<u>Notes</u>: 1. Derate linearly @ $4.57 \text{ mW/}^{\circ}\text{C}$ for $T_A > +25 ^{\circ}\text{C}$.

2. Derate linearly @ 28.5 mW/°C for $T_C > +25$ °C

MSC – Lawrence

6 Lake Street, Lawrence, MA 01841 Tel: 1-800-446-1158 or (978) 620-2600 Fax: (978) 689-0803

MSC - Ireland

Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

Website:

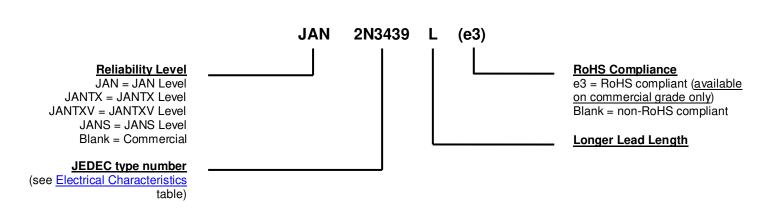
www.microsemi.com



MECHANICAL and PACKAGING

- CASE: Hermetically sealed, kovar base, nickel cap.
- TERMINALS: Tin/lead plate or RoHS compliant matte/tin (commercial grade only) over nickel.
- MARKING: Part number, date code, manufacturer's ID.
- POLARITY: NPN (see package outline).
- WEIGHT: Approximately 1.14 grams.
- See Package Dimensions on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS				
Symbol	Definition			
C _{obo}	Common-base open-circuit output capacitance.			
I _{CEO}	Collector cutoff current, base open.			
I _{CEX}	Collector cutoff current, circuit between base and emitter.			
I _{EBO}	Emitter cutoff current, collector open.			
h _{FE}	Common-emitter static forward current transfer ratio.			
$V_{\sf CEO}$	Collector-emitter voltage, base open.			
V_{CBO}	Collector-emitter voltage, emitter open.			
V _{EBO}	Emitter-base voltage, collector open.			



ELECTRICAL CHARACTERISTICS (T_A = +25°C, unless otherwise noted)

OFF CHARACTERISTICS

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mA}$ $R_{BB1} = 470 \Omega$; $V_{BB1} = 6 \text{ V}$ $L = 25 \text{ mH (min)}$; $f = 30 - 60 \text{ Hz}$	2N3439L 2N3440L	V _{(BR)CEO}	350 250		V
Collector-Emitter Cutoff Current V _{CE} = 300 V V _{CE} = 200 V	2N3439L 2N3440L	I _{CEO}		2.0 2.0	μА
Emitter-Base Cutoff Current V _{EB} = 7.0 V		I _{EBO}		10	μΑ
Collector-Emitter Cutoff Current $V_{CE} = 450 \text{ V}, V_{BE} = -1.5 \text{ V}$ $V_{CE} = 300 \text{ V}, V_{BE} = -1.5 \text{ V}$	2N3439L 2N3440L	I _{CEX}		5.0 5.0	μΑ
Collector-Base Cutoff Current $V_{CB} = 360 \text{ V}$ $V_{CB} = 250 \text{ V}$ $V_{CB} = 450 \text{ V}$ $V_{CB} = 300 \text{ V}$	2N3439L 2N3440L 2N3439L 2N3440L	І _{СВО}		2.0 2.0 5.0 5.0	μΑ

ON CHARACTERISTICS (1)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Forward-Current Transfer Ratio $I_C = 20$ mA, $V_{CE} = 10$ V $I_C = 2.0$ mA, $V_{CE} = 10$ V $I_C = 0.2$ mA, $V_{CE} = 10$ V	h _{FE}	40 30 10	160	
Collector-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 4.0 \text{ mA}$	V _{CE(sat)}		0.5	V
Base-Emitter Saturation Voltage $I_C = 50 \text{ mA}, I_B = 4.0 \text{ mA}$	V _{BE(sat)}		1.3	V

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}, f = 5.0 \text{ MHz}$	h _{fe}	3.0	15	
Forward Current Transfer Ratio $I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$	h _{fe}	25		
Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	C _{obo}		10	pF
Input Capacitance $V_{CB} = 5.0 \text{ V}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	C _{ibo}		75	pF

NOTES: (1) Pulse Test: Pulse Width = 300 µs, duty cycle ≤ 2.0%



ELECTRICAL CHARACTERISTICS (T_A = +25°C, unless otherwise noted) continued

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-On Time $V_{CC} = 200 \text{ V}; I_C = 20 \text{ mA}, I_{B1} = 2.0 \text{ mA}$	t _{on}		1.0	μs
Turn-Off Time $V_{CC} = 200 \text{ V}; I_C = 20 \text{ mA}, I_{B1} = -I_{B2} = 2.0 \text{ mA}$	t _{off}		10	μs

SAFE OPERATING AREA (See graph below and also reference test method 3053 of MIL-STD-750.)

DC Tests

 $T_C = +25 \, ^{\circ}C$, 1 Cycle, $t = 1.0 \, s$

Test 1

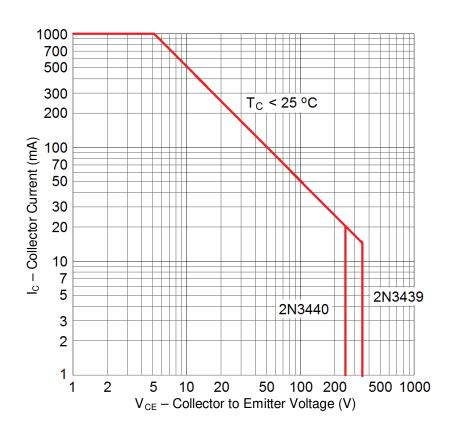
 $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ A}$ Both Types

Test 2

 $V_{CE} = 350 \text{ V}, I_{C} = 14 \text{ mA}$ 2N3439L

Test 3

 $V_{CE} = 250 \text{ V}, I_{C} = 20 \text{ mA}$ 2N3440L



Maximum Safe Operating graph (continuous dc)



GRAPHS

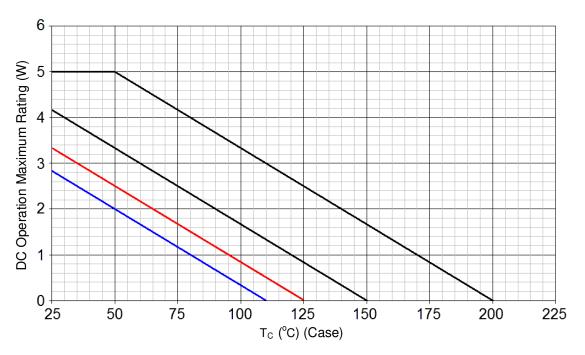


FIGURE 1

Temperature-Power Derating Curve

NOTES: Thermal Resistance Junction to Case = 30.0 °C/W

Max Finish-Alloy Temp = 175.0 °C

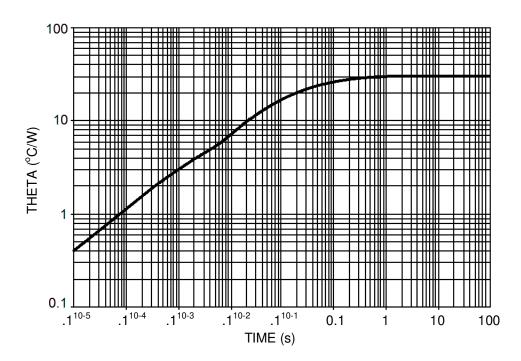


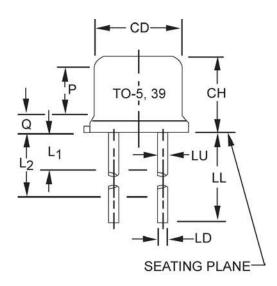
FIGURE 2

Maximum Thermal Impedance

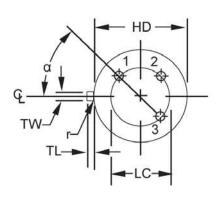
NOTE: $T_C = +25$ °C, $P_T = 5.0$ W, thermal resistance $R_{\theta JC} = 30$ °C/W, steel.



PACKAGE DIMENSIONS



Dimensions						
Symbol	Incl	Inches		Millimeters		
	Min	Max	Min	Max		
CD	.305	.335	7.75	8.51	6	
CH	.240	.260	6.10	6.60		
HD	.335	.370	8.51	9.40		
LC	.200) TP	5.08	3 TP	7	
LD	.016	.019	0.41	0.48	8,9	
LL	See note 14					
LU	.016	.019	0.41	0.48	8,9	
L1		.050		1.27	8,9	
L2	.250		6.35		8,9	
Р	.100		2.54		7	
Q		.030		0.76	5	
TL	.029	.045	0.74	1.14	3,4	
TW	.028	.034	0.71	0.86	3	
r		.010		0.25	10	
α	45°	45° TP		45° TP		



NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- 4. Dimension TL measured from maximum HD.
- 5. Body contour optional within zone defined by HD, CD, and Q.
- 6. CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- 7. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by gauging procedure.
- 8. Dimension LU applies between L1 and L2. Dimension LD applies between L2 and LL minimum. Diameter is uncontrolled in and beyond LL minimum.
- 9. All three leads.
- 10. The collector shall be internally connected to the case.
- 11. Dimension r (radius) applies to both inside corners of tab.
- 12. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
- 13. Lead 1 = emitter, lead 2 = base, lead 3 = collector.
- 14. For transistor types 2N3439L and 2N3440L (TO-5), dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max.